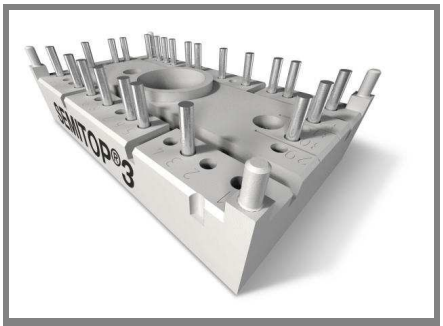


SEMITOP® 3

IGBT Module

SK150GB066T

Target Data

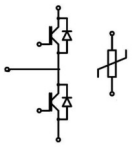
Features

- Compact design
- One scre mounting
- Heat transfer and isolation trough direct copper bonded aluminium oxide ceramic (DCB)
- Trench IGBT technology
- CAL HD technology FWD
- Integrated NTC temperature sensor

Typical Applications*

Remarks

- V_{isol} = 3000V AC,50Hz,1s



GB-T

Absolute Maximum Ratings			T_s = 25 °C, unless otherwise specified	
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		600	V
I_C	T_j = 175 °C	T_s = 25 °C	124	A
		T_s = 70 °C	96	A
I_{CRM}	I_{CRM}= 2 x I_{Cnom}		300	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 360 V; $V_{GE} \leq$ 20 V; V_{CES} < 600 V	T_j = 150 °C	6	µs
Inverse Diode				
I_F	T_j = 175 °C	T_s = 25 °C	135	A
		T_s = 70 °C	95	A
I_{FRM}	I_{FRM}= 2 x I_{Fnom}		300	A
Module				
$I_{t(RMS)}$				A
T_{vj}			-40 ... +175	°C
T_{stg}			-40 ... +125	°C
V_{isol}	AC, 1 min.		2500	V

Characteristics			T_s = 25 °C, unless otherwise specified			
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 2,4 mA		5	5,8	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C			0,0076	mA
		T_j = 125 °C				mA
I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V	T_j = 25 °C			1200	nA
		T_j = 125 °C				nA
V_{CE0}		T_j = 25 °C		0,8	1,1	V
		T_j = 150 °C		0,7	1	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		4	5	mΩ
		T_j = 150°C		6,35	7	mΩ
$V_{CE(sat)}$	I_{Cnom} = 150 A, V_{GE} = 15 V	T_j = 25°$C_{chiplev.}$		1,45	1,85	V
		T_j = 150°$C_{chiplev.}$		1,65	2,05	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		9,4		nF
C_{oes}				0,6		nF
C_{res}				0,29		nF
Q_G	V_{GE}= -7V...+15V			1400		nC
$t_{d(on)}$	R_{Gon} = 8 Ω	V_{CC} = 300V		95		ns
t_r	di/dt = 2250 A/µs	I_C= 150A		50		ns
E_{on}		T_j = 150 °C		6,25		mJ
$t_{d(off)}$	R_{Goff} = 8 Ω	V_{GE}= -7/+15 V		541		ns
t_f	di/dt = 2250 A/µs			70		ns
E_{off}				5,7		mJ
$R_{th(j-s)}$	per IGBT			0,65		K/W

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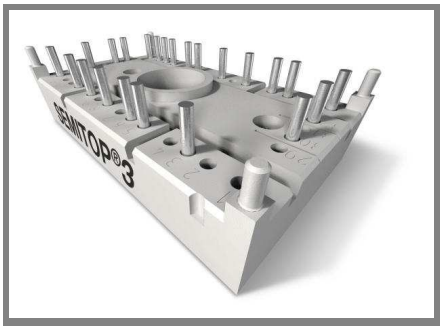

SEMITOP® 3

IGBT Module

SK150GB066T

Target Data

Features

- Compact design
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- Heat transfer and isolation trough direct copper bonded aluminium oxide ceramic (DCB)
- Trench IGBT technology
- CAL HD technology FWD
- Integrated NTC temperature sensor

Typical Applications*

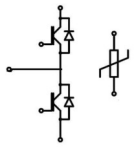
Remarks

- V_{isol} = 3000V AC,50Hz,1s

Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 150 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		1,35		V
		T_j = 150 °$C_{chiplev.}$		1,31		V
V_{F0}		T_j = 25 °C				V
		T_j = 150 °C		0,85		V
r_F		T_j = 25 °C				mΩ
		T_j = 150 °C		3,9		mΩ
I_{RRM}	I_F = 150 A	T_j = 150 °C		100		A
Q_{rr}	di/dt = 2250 A/µs			11		µC
E_{rr}	V_{CC}= 300V			1,7		mJ
$R_{th(j-s)D}$	per diode			0,73		K/W
M_s	to heat sink		2,5		2,75	Nm
w				60		g
Temperature sensor						
R_{100}	T_s = 100°C (R_{25}=5kΩ)			493±5%		Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



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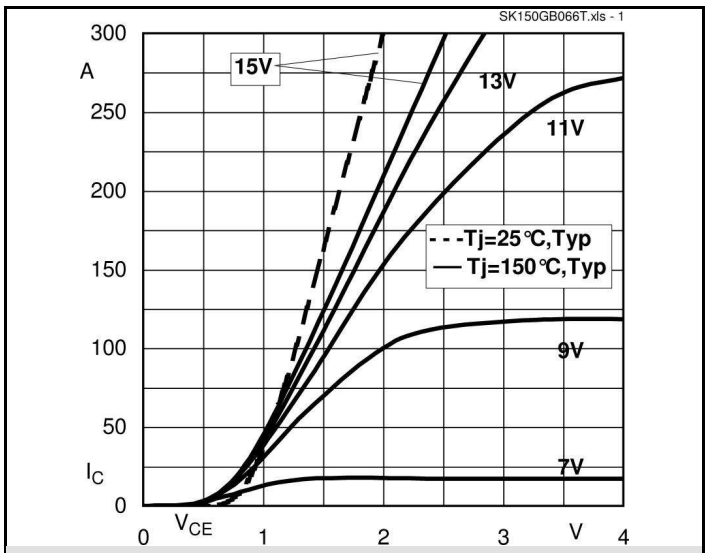

Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

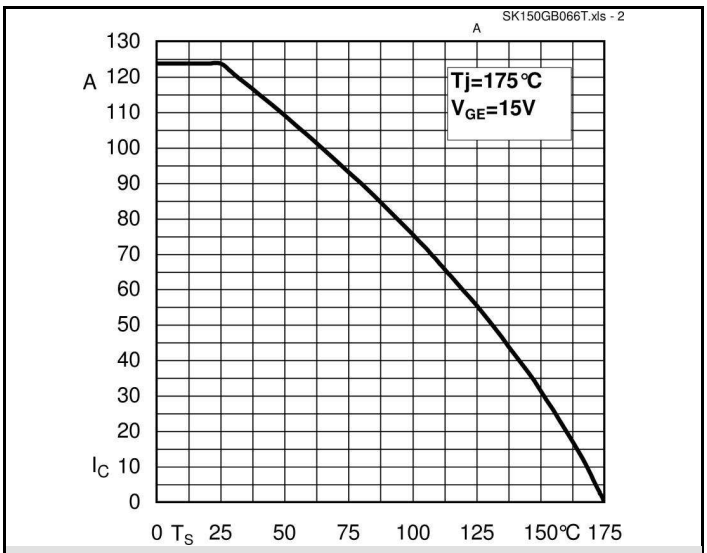

Fig. 2 Rated current vs. temperature $I_C = f(T_s)$

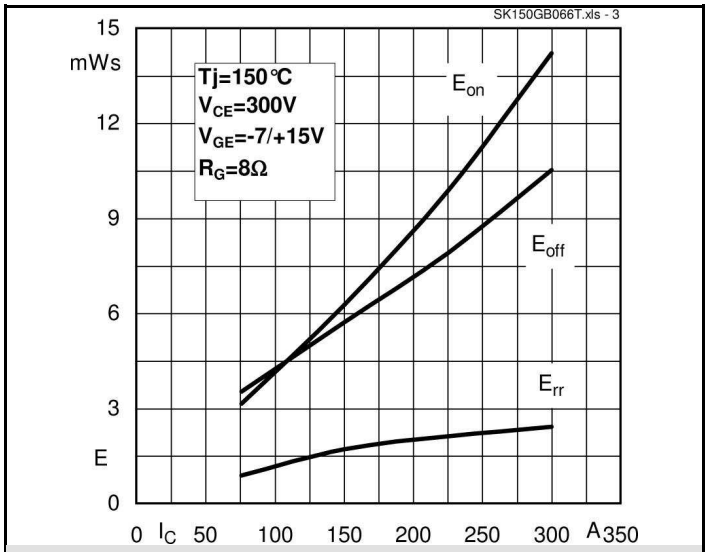

Fig. 3 Typ. turn-on /-off energy = f (I_C)

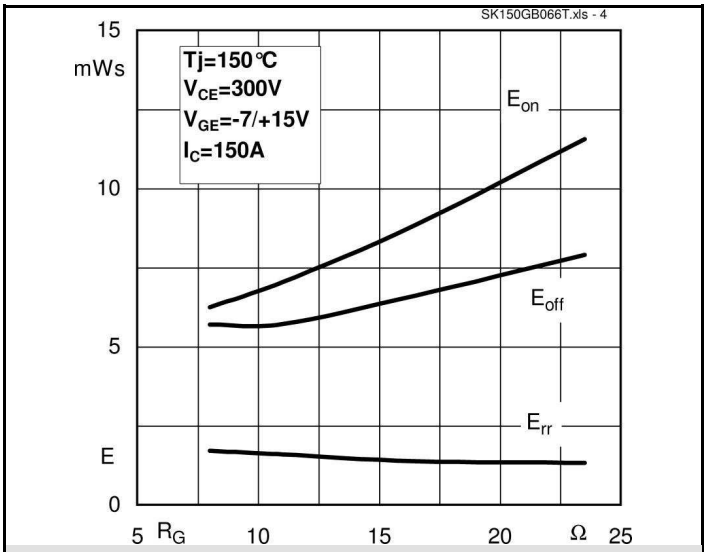

Fig. 4 Typ. turn-on /-off energy = f (R_G)

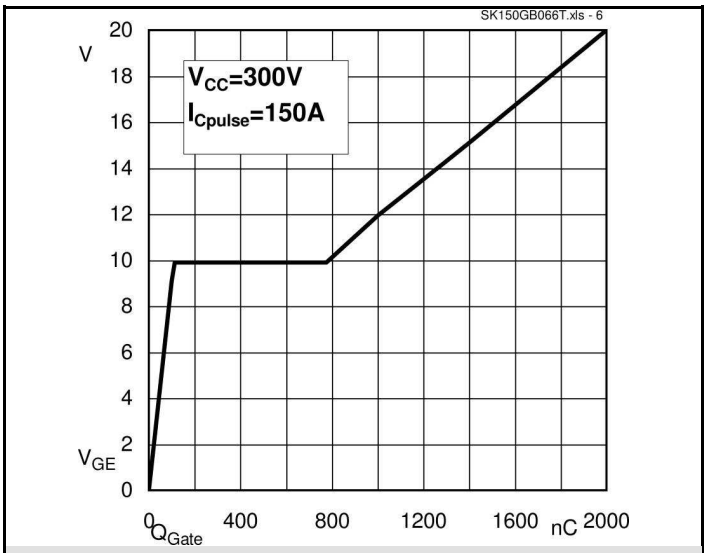

Fig. 6 Typ. gate charge characteristic

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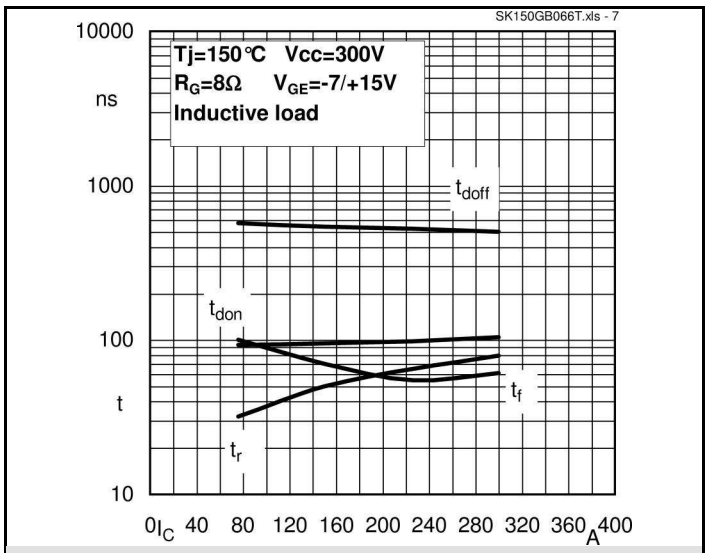

Fig. 7 Typ. switching times vs. I_C

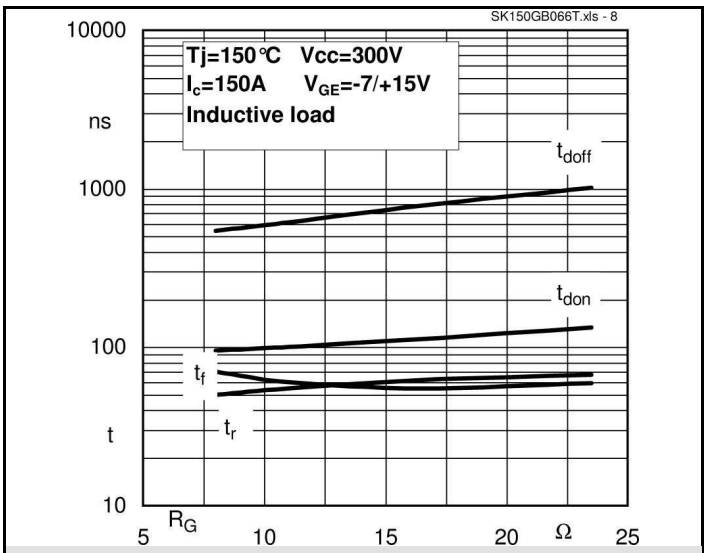

Fig. 8 Typ. switching times vs. gate resistor R_G

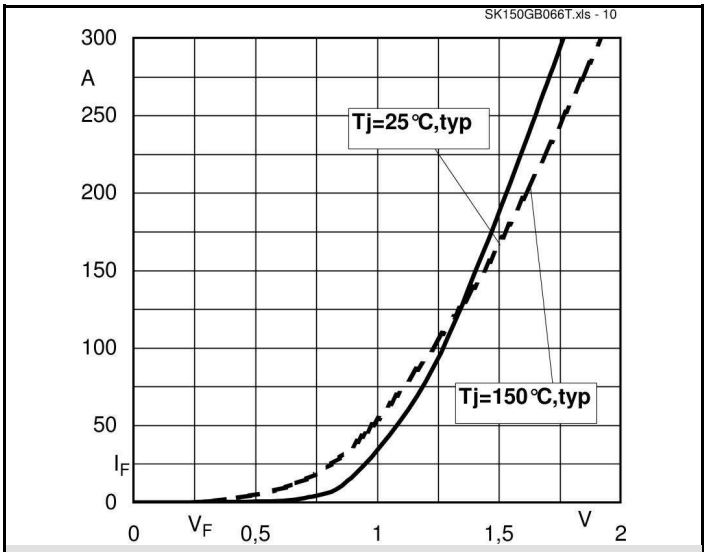

Fig. 10 CAL diode forward characteristic

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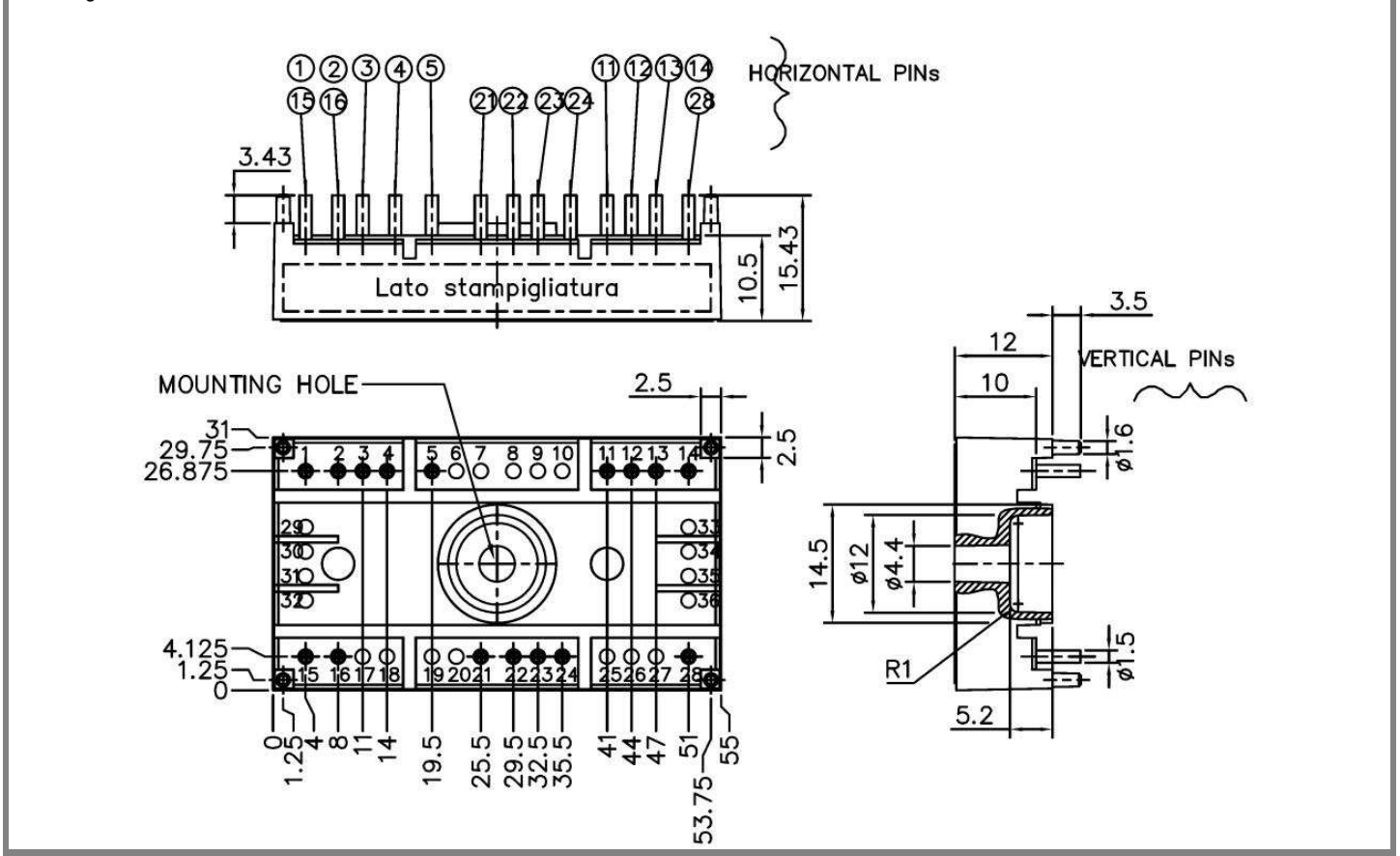
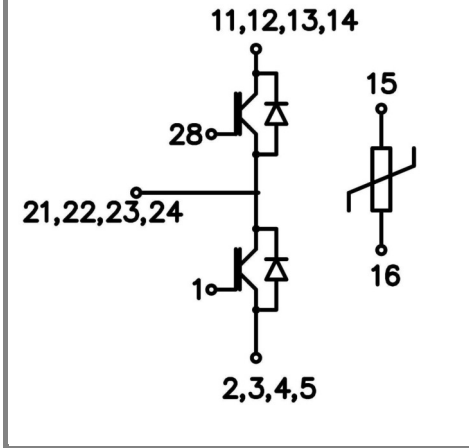


Case T73 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T 73 GB-T

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